

SEMICONDUCTOR DEVICE HAVING SILICIDE LAYERS AND METHOD OF FABRICATING THE SAME

ABSTRACT OF THE DISCLOSURE

5 Some embodiments include an isolation layer defining an active region of a substrate,
a gate pattern formed on the active region, and source/drain regions formed in the active
region. Sidewall spacers are formed on sidewalls of the gate pattern, and a blocking
insulation layer is formed on the isolation layer and on a portion of the active region
neighboring the isolation layer. A silicide layer is formed on source/drain regions between the
10 blocking insulation layer and the sidewall spacers. Some embodiments include defining an
active region of a substrate using an isolation layer, forming a gate pattern on the active
region, implanting impurities into the active region, and forming a spacer insulation layer on
a surface of the substrate with the gate pattern. A region of the spacer insulation layer
becomes thinner the closer it is to the gate pattern. Other embodiments are described in the
15 claims.